

ABSTRACT

In a plasma CVD apparatus for applying a film deposition process to a semiconductor wafer (W), a wafer
5 placement stage (3) is provided at a center of a vacuum chamber (2). The placement stage (3) is mounted to a side wall (63) via a support part (6). An exhaust port (9) having a diameter equal to or smaller than a diameter of the placement stage (3) is provided under the placement
10 stage (3). A center axis (C1) of the exhaust port (9) is displaced from a center axis of the placement stage (3) in a direction opposite to an extending direction of the support part (6), thereby achieving an efficient exhaust.